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Title: Fudan Energy Storage Device

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The breakthrough device supports eight-bit instruction operations and 32-bit high-speed parallel operations with random access, ...

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The breakthrough device supports eight-bit instruction operations and 32-bit high-speed parallel operations with random access, achieving a 94.3 percent memory cell yield.

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Researchers from Shanghai-based Fudan University have developed a picosecond-level flash memory device with an ...

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